



# Some non-resolved problems on LIBS plasmas

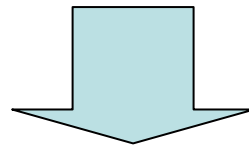
**DEN Saclay/DPC/SCP/LILM**

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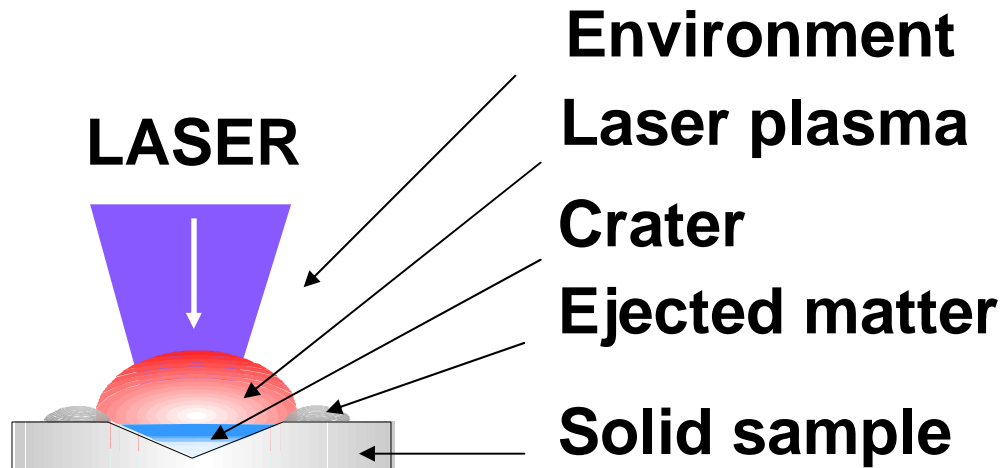
## Problems to be discussed

- 1) Environment effect on the LIBS signal (theses of M. Autin, of C. Gautier; CEA patent)
- 2) LIBS signal lifetime (theses of V. Detalle, of B. Sallé, of J. Gaudin)
- 3) LIBS plasma stoichiometry or “matrix effect” (theses of C. Nouvellon, of R. Bruder)
- 4) fs/ps-double pulse LIBS (PostDoc of C. Dutouquet)



## Laser Plasma Chemistry and Dusts (nano/micro-particles) in Laser Plasmas

(theses of F. Chartier, of F. Brygo, of P. Dewalle)



LA properties = f (E,  $\emptyset$ ,  $\Delta t$ ,  $\lambda$ ,  $\Delta\theta$ , polarisation, sample, air,...)

Analytical signal  $\sim N_{abl} \cdot \alpha \cdot A_{ij} \cdot \exp(E_i/kT) \cdot t_p \cdot K_d$

$N_{abl} \sim (V_c - V_r) \cdot$  ablation efficiency (not atomisation one!)

$\alpha$  is atomisation efficiency

$t_p$  is  $\sim 100$  ns for micro and  $\sim 1$   $\mu$ s for macrosampling



## 1. Environment effect on the LIBS signal

(theses of M. Autin, of C. Gautier; CEA patent )



## 1. Environment effect on the LIBS signal

1.1. Optimal pressure ~ 10 mBar

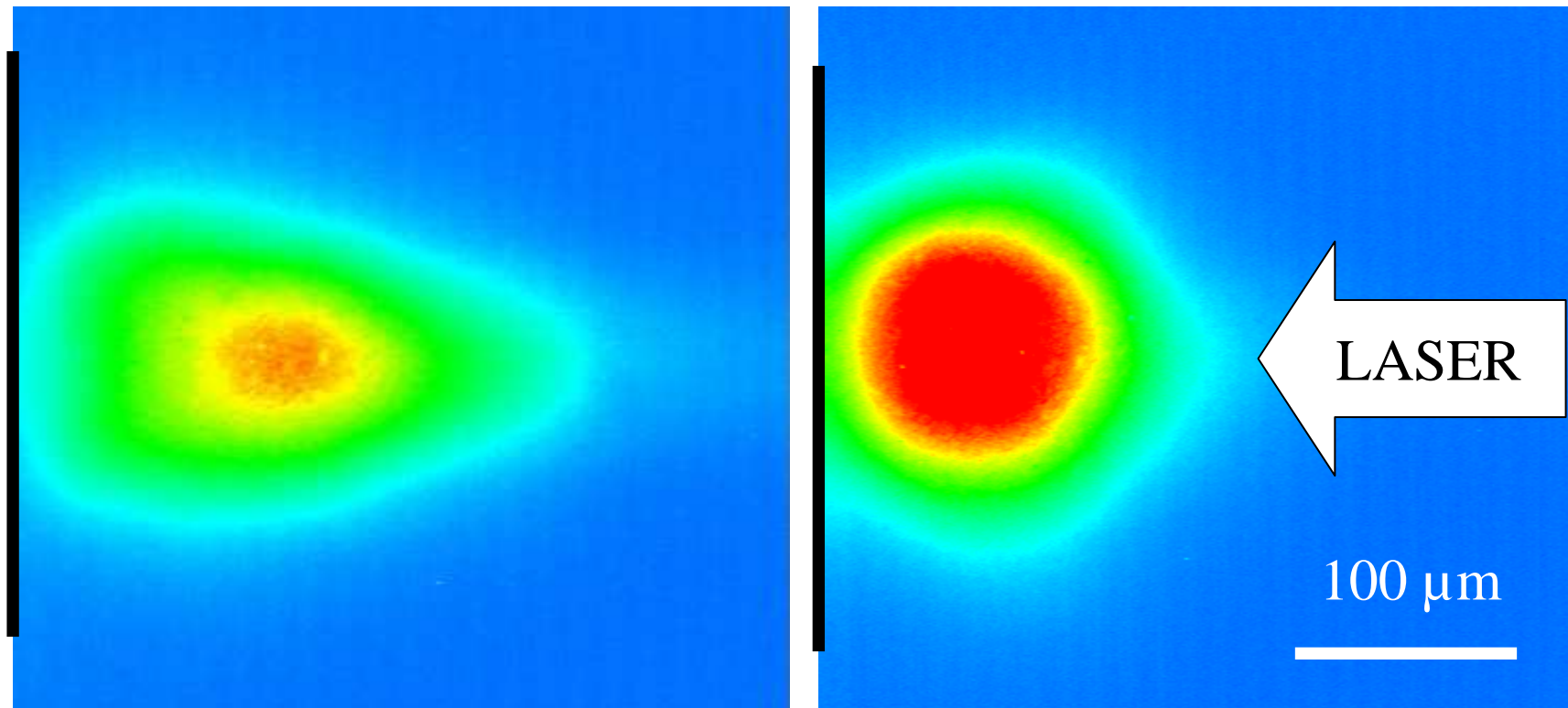
1.2. ns-double pulse LIBS

1.3. Jet of Argon gives rise to the LIBS signal



## 1. Environment effect on the LIBS signal

**Target:** Al + 10%Cu; **Laser:** 50 fs, 800 nm, 100  $\mu$ J, diameter 15  $\mu$ m; **CCD:** gate 1000 ns, delay 50 ns

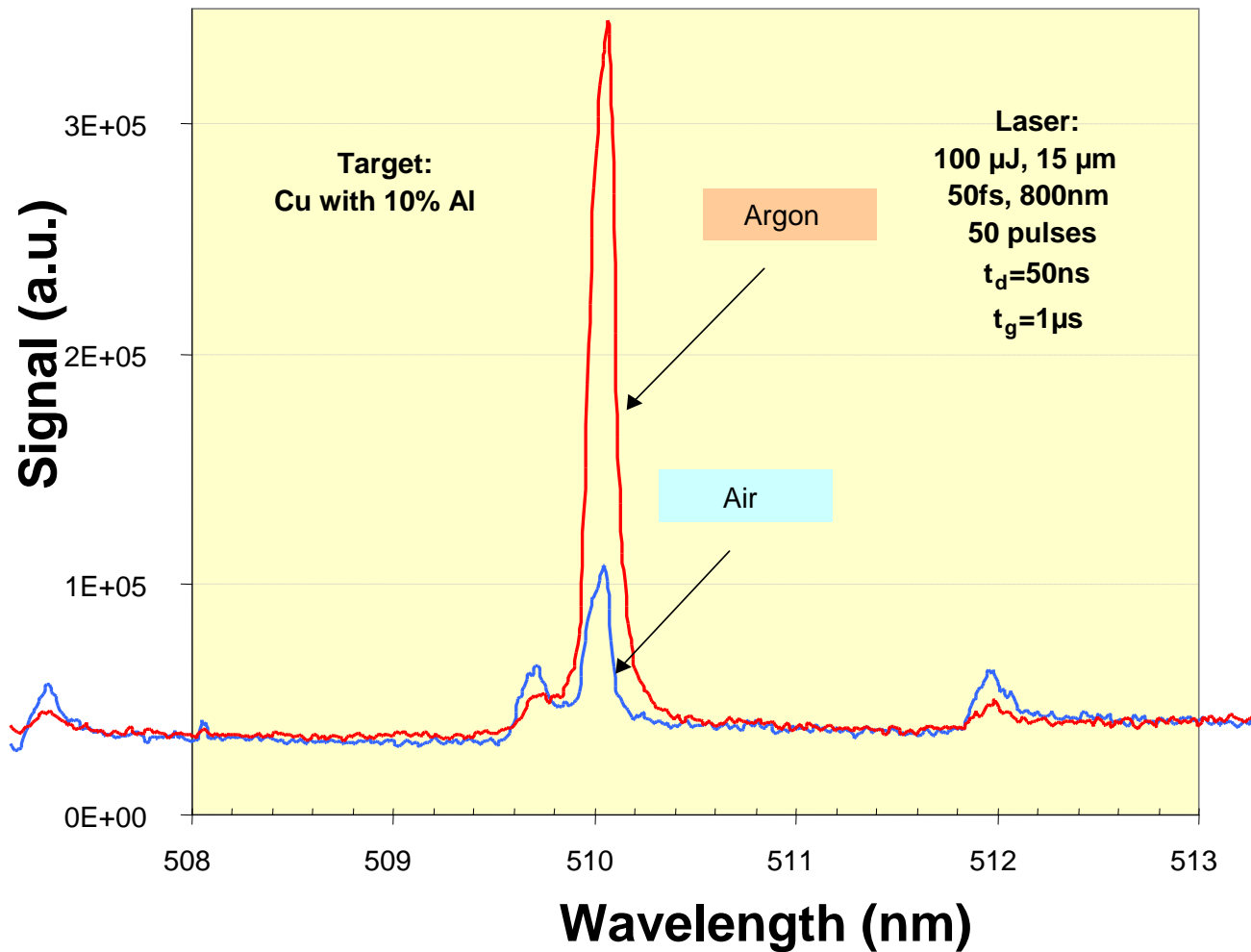


Air, 1 atm

Ar, 1 atm



## 1. Environment effect on the LIBS signal



gain  $\cong$  5



## 2. LIBS signal lifetime

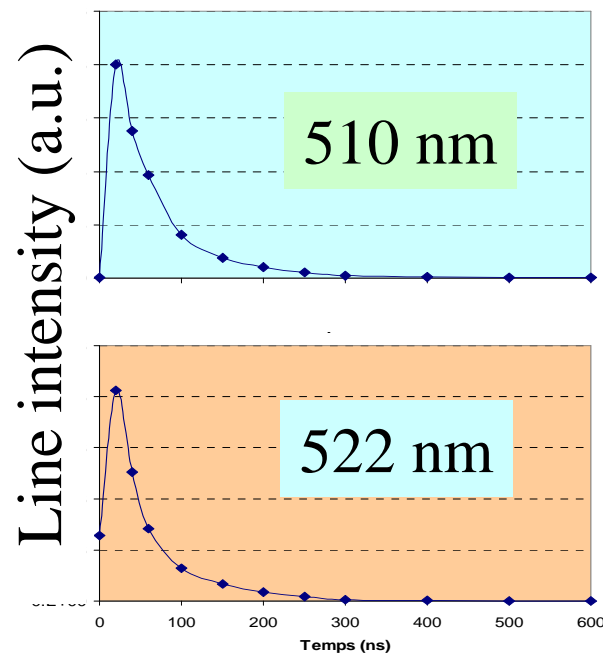
(theses of V. Detalle, of B. Sallé, of J. Gaudin)



## 2. LIBS signal lifetime

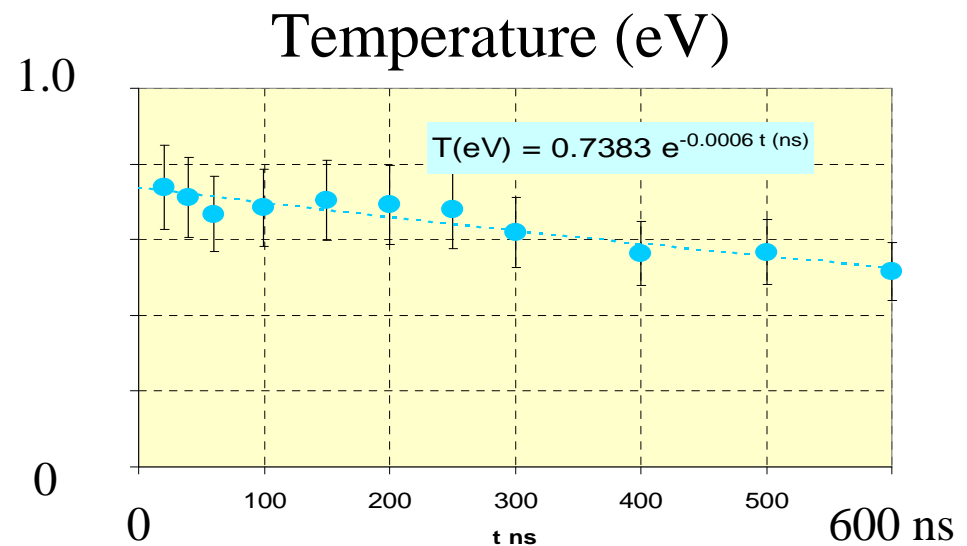
$$\text{Signal}(t) \sim N_a(t) \cdot \exp[E_i/kT(t)] \cdot u^{-1}(t)$$

LTE and excitation temperature



0 ns

600 ns

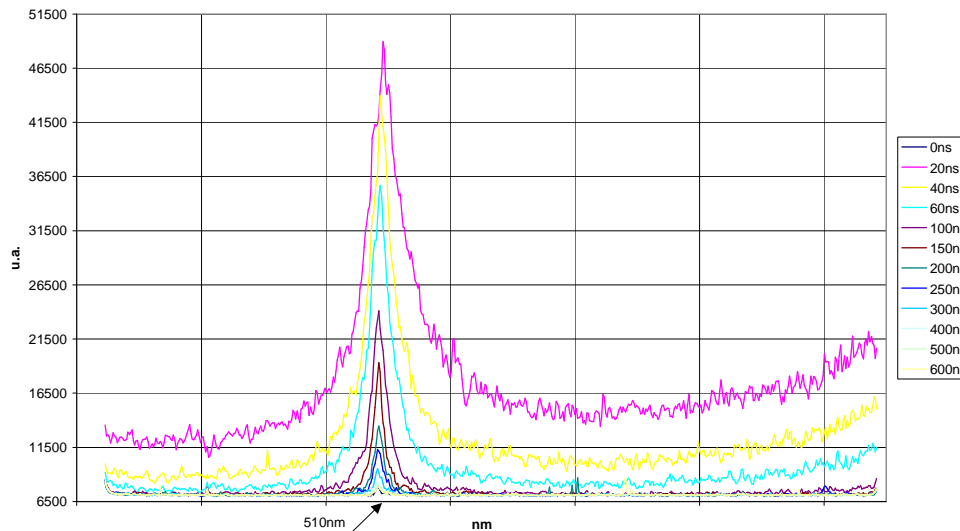




## 2. LIBS signal lifetime

### Stark broadening and electron density

CuI 510 nm line broadening

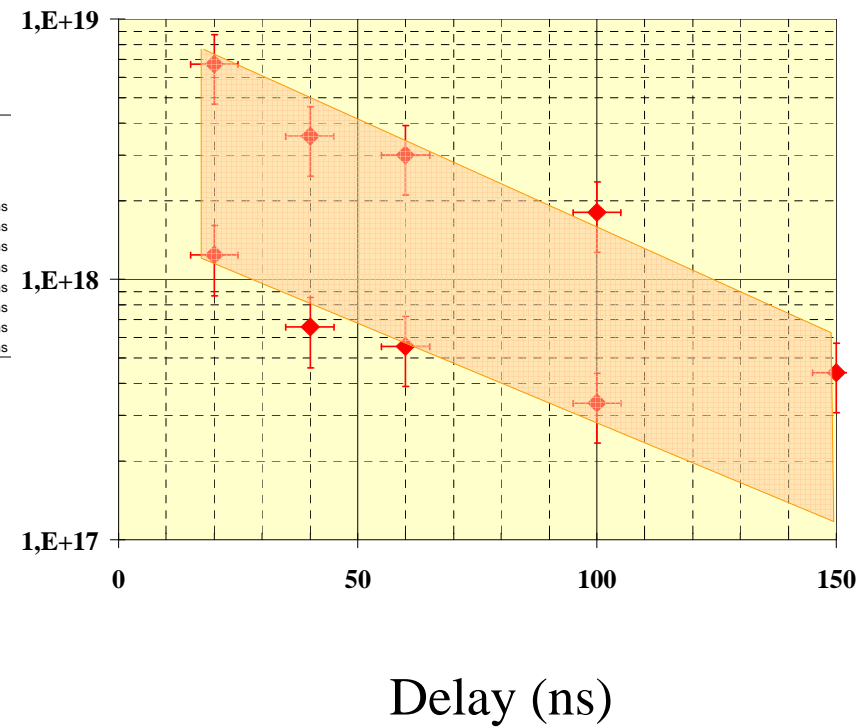


$$\Delta \lambda = 11.4 \cdot C_4^{2/3} \cdot \bar{v}_e^{1/3} \cdot N_e \cdot \frac{\lambda^2}{2\pi c}$$

$$[C_4] = \text{cm}^4 \cdot \text{s}^{-1}$$

$$\bar{v}_e = \sqrt{\frac{8kTe}{\pi m_e}}$$

Electron density of fs-laser plasma



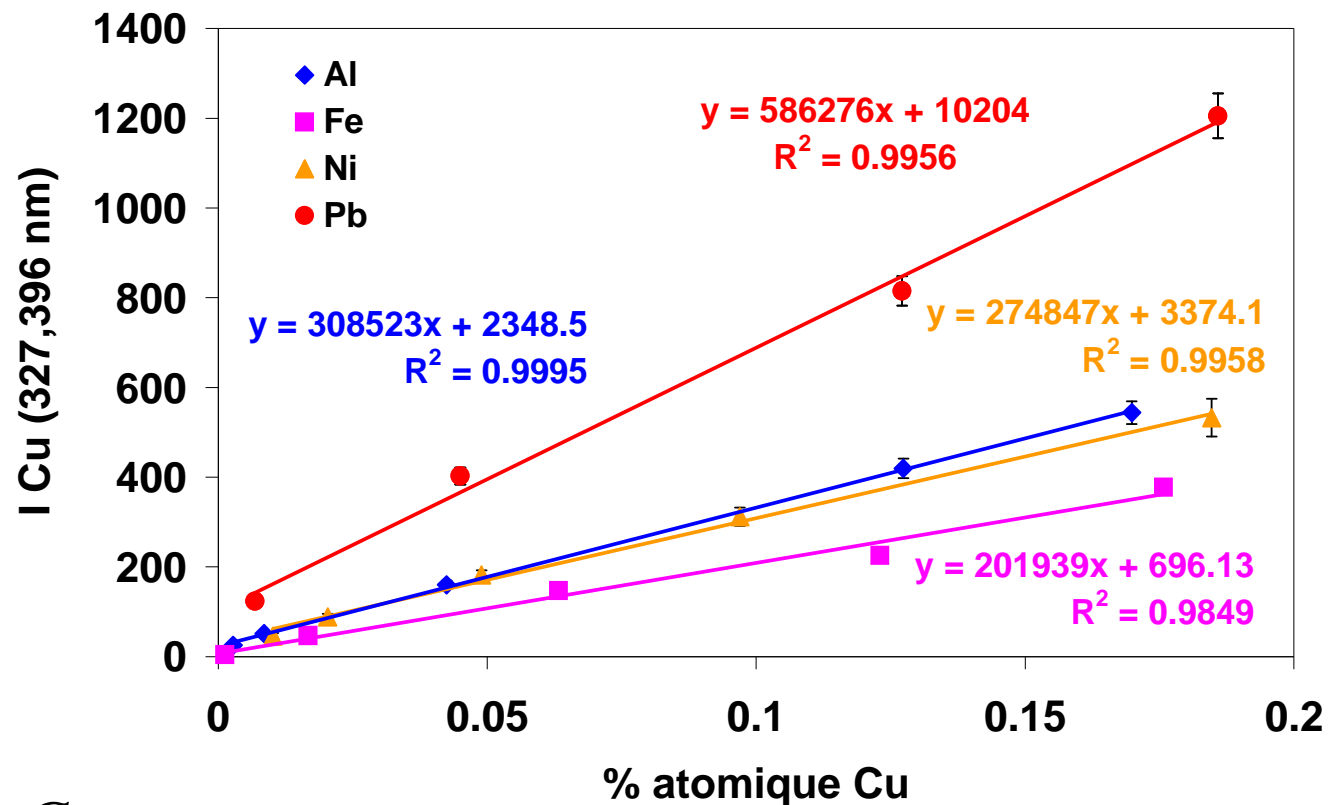


## 3. LIBS plasma stoichiometry or “matrix effect”

(theses of C. Nouvellon, of R. Bruder)



## 3. LIBS plasma stoichiometry or “matrix effect”



$$I_{327,396nm}^{Cu} \propto C_{Cu}$$

Cu : 327,396 nm ; 30 spectra per etalon

Fluency : 15 J.cm<sup>-2</sup> ; Delay : 700 ns ; Gate width : 4,5µs ; 30 shots per spectrum



## 3. LIBS plasma stoichiometry or “matrix effect”

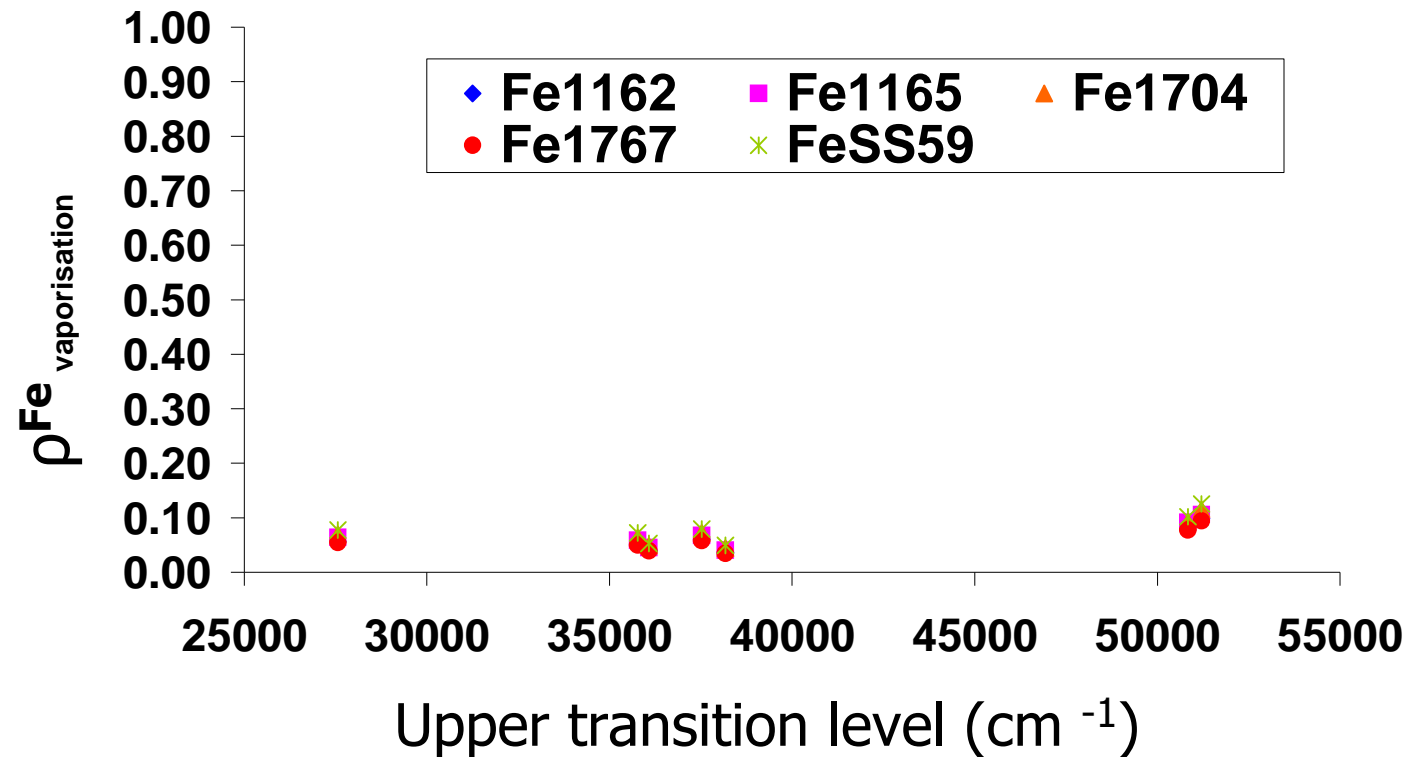
- $$\rho^{Cu}_{atomisation} = N_{Cu \text{ in plasma atomic vapour}} / N_{Cu \text{ ablated}}$$

- Determination of  $\rho^{Cu}_{atomisation}$  requires the detection scheme calibration with an etalon source of photons (lamp-etalon)

$$\rho^{Cu}_{atomisation} = \frac{I_{photons}^{Cu} \times U_{Cu}(T)}{f(\lambda_{ij}) \times (1 - \tau^{Cu}_i) \times C_{Cu} \times N_0 \times g_i \times A_{ij} \times e^{-E_i/kT}}$$



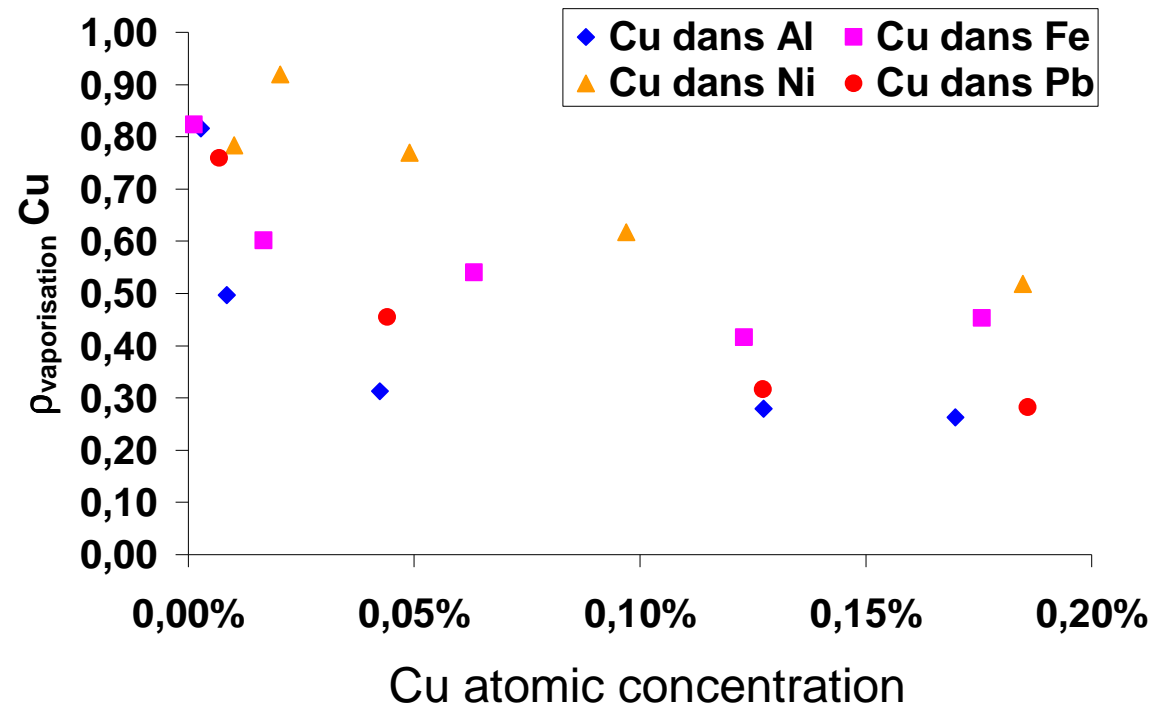
## 3. LIBS plasma stoichiometry or “matrix effect”



→  $\rho$  atomisation for the matrix atoms is low



## 3. LIBS plasma stoichiometry or “matrix effect”



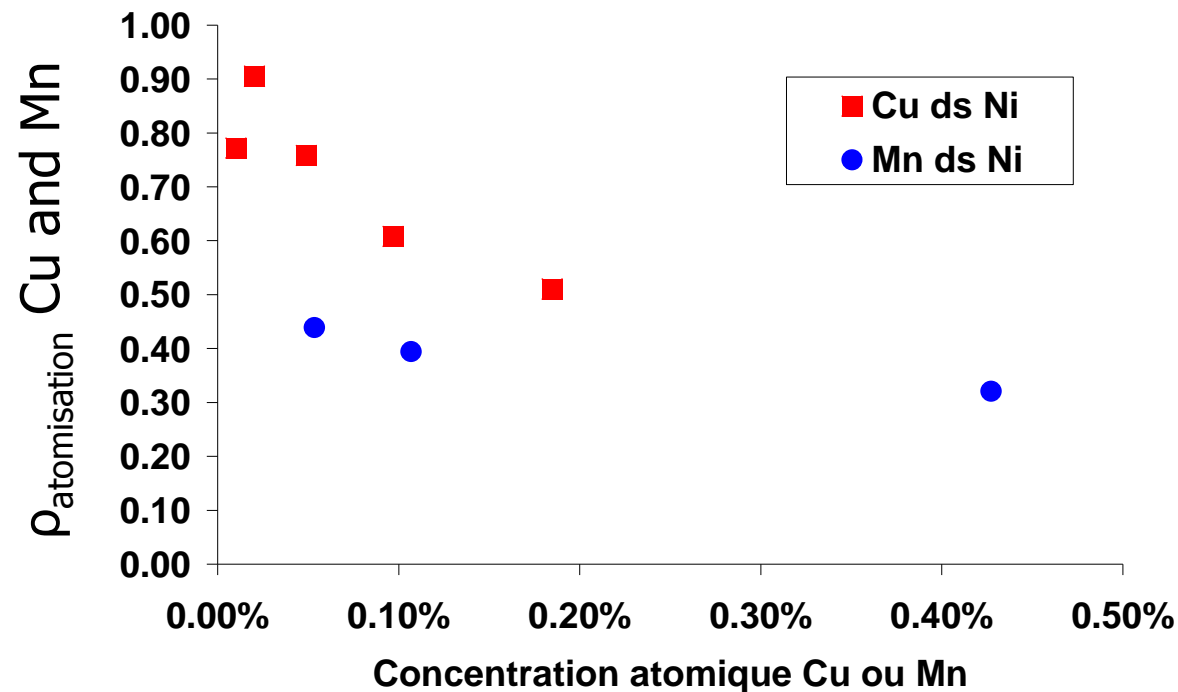
→  $P_{\text{atomisation}}$  is a function of a matrix

→  $P_{\text{atomisation}}$  is decreasing with the impurity concentration increase



## 3. LIBS plasma stoichiometry or “matrix effect”

- Element influence



$P_{\text{atomisation}}$  is a function of the elements



## 3. LIBS plasma stoichiometry or “matrix effect”

### Summary

- The presence of the matrix effect for the metal samples and non-efficient correction by  $N_0$ ,  $T$  et  $N_e$
- Atomisation efficiency for the matrix is low
- Atomisation efficiency is a function of the element and its concentration

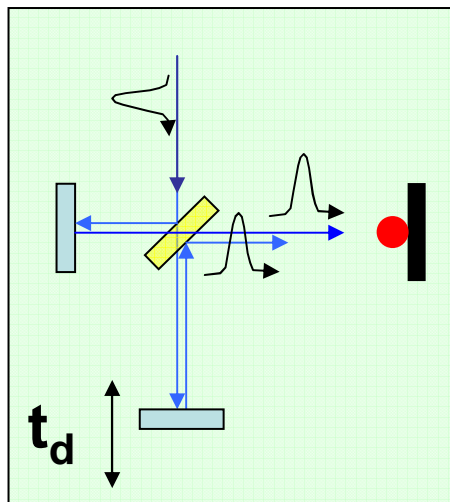


## 4. fs/ps-double pulse LIBS

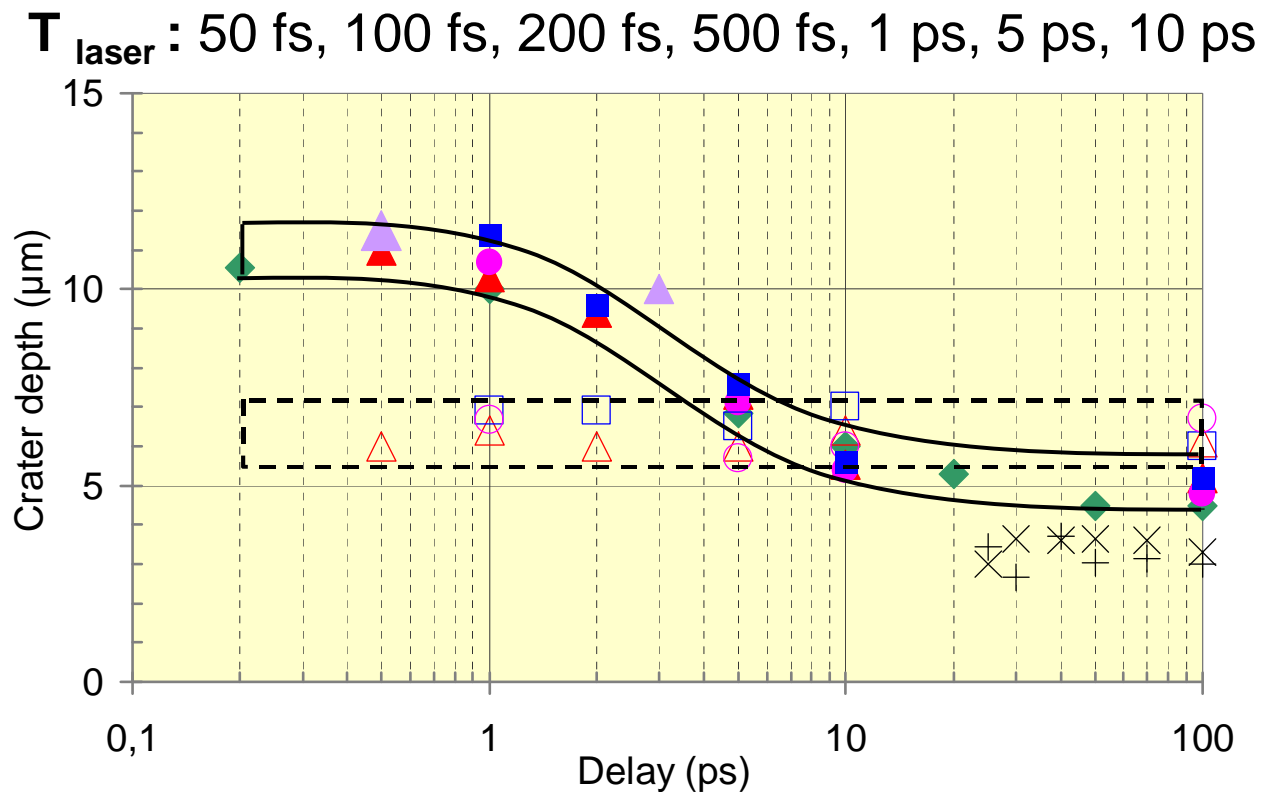
(PostDoc of C. Dutouquet)



## 4. fs/ps-double pulse LIBS



Target – Cu/Al, air  
E = 20  $\mu$ J x 2



◆ do not strongly depend on metal (Cu and Al)

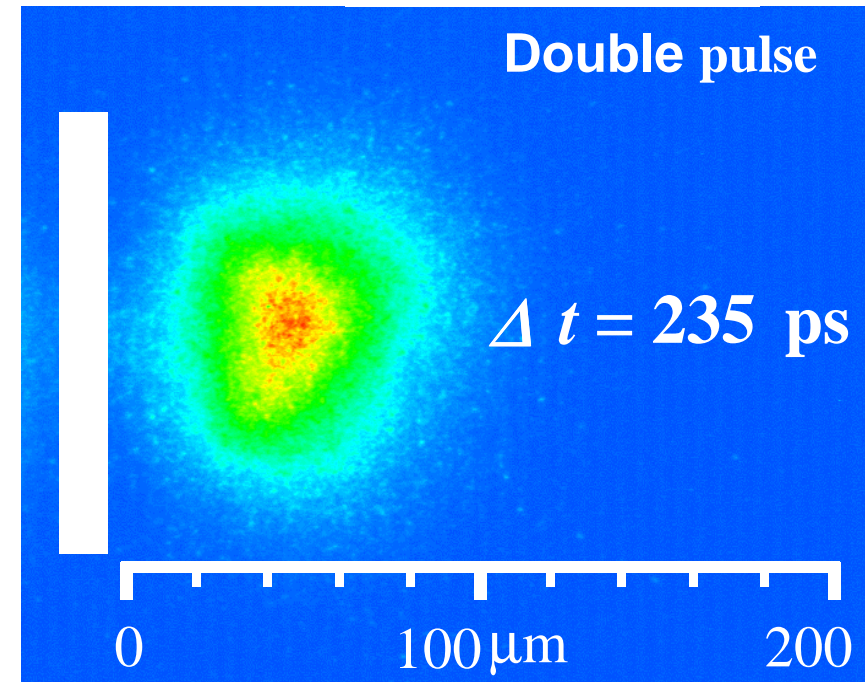
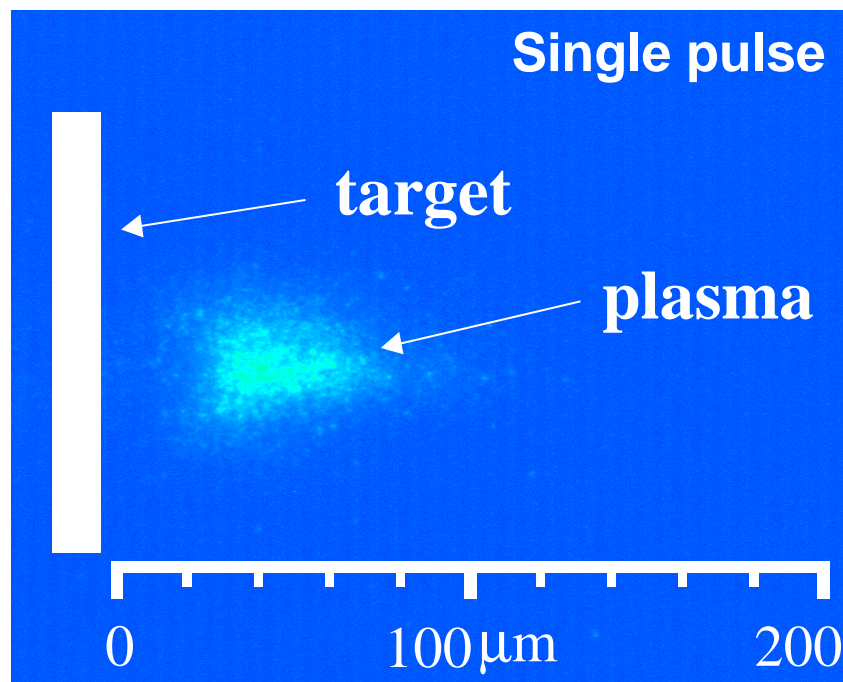


## 4. fs/ps-double pulse LIBS

$$E_{\text{single pulse}} = 20 \mu\text{J}$$

$$E_{\text{double pulse}} = 2 \times 20 \mu\text{J}$$

- ◆ Delay 3ns
- ◆ Gate width 1  $\mu\text{s}$
- ◆ Attenuators  $T = 2 \%$
- ◆ High CCD gain



**PLASMA LUMINOSITY IS HIGHER WITH THE DOUBLE PULSE**



## 4. fs/ps-double pulse LIBS

### Simulation of ultrashort double pulse laser ablation of metals

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## Two-temperature multi-material Eulerian hydrodynamics



### Basic equations

$$\frac{\partial f^\alpha}{\partial t} + \nabla \cdot (f^\alpha \mathbf{u}) - \frac{f^\alpha \bar{K}_S}{K_S^0} \nabla \cdot \mathbf{u}$$

$$\frac{\partial (f^\alpha \rho^\alpha Z^\alpha)}{\partial t} + \nabla \cdot (f^\alpha \rho^\alpha Z^\alpha \mathbf{u}) - f^\alpha m_i^0 S^\alpha$$

$$\frac{\partial (f^\alpha \rho^\alpha)}{\partial t} + \nabla \cdot (f^\alpha \rho^\alpha \mathbf{u}) = 0$$

$$\frac{\partial (\bar{\rho} \mathbf{u})}{\partial t} + \nabla \cdot (\bar{\rho} \mathbf{u} \otimes \mathbf{u}) - \nabla \bar{P} = 0$$

$$\frac{\partial}{\partial t} \left[ f^\alpha \rho^\alpha \left( E_\alpha + \frac{|\mathbf{u}|^2}{2} \right) \right] + \nabla \cdot \left[ f^\alpha \rho^\alpha \left( E_\alpha + \frac{|\mathbf{u}|^2}{2} \right) \mathbf{u} \right] - \frac{f^\alpha \rho^\alpha}{\bar{\rho}} \nabla \bar{P} \cdot \mathbf{u} -$$

$$- \bar{P}_\alpha \frac{f^\alpha \bar{K}_S}{K_S^0} \nabla \cdot \mathbf{u} - \boxed{f^\alpha Q_{ei}^\alpha} + \boxed{Q_L^\alpha} + \boxed{\frac{f^\alpha \rho^\alpha C_{v,i}^\alpha}{\bar{\rho} C_{v,i}^\alpha} \nabla \cdot (\bar{\rho}_i \nabla T_i)} + \boxed{f^\alpha Q_j^\alpha} - \boxed{f^\alpha Q_{rad}^\alpha}$$

$$\frac{\partial (f^\alpha \rho^\alpha E_{i,\alpha}^\alpha)}{\partial t} + \nabla \cdot (f^\alpha \rho^\alpha E_{i,\alpha}^\alpha \mathbf{u}) - \bar{P}_\alpha \frac{f^\alpha \bar{K}_S}{K_S^0} \nabla \cdot \mathbf{u} + \boxed{f^\alpha Q_{i,\alpha}^\alpha}$$

$$E_{i,\alpha}^\alpha(\rho, T) \rightarrow E_{i,\alpha}^\alpha, C_{v,i}^\alpha, P_{i,\alpha}^\alpha, K_{i,S}^\alpha$$

$$E_{e,\alpha}^\alpha(\rho, T_e) \rightarrow E_{e,\alpha}^\alpha, C_{v,e}^\alpha, P_{e,\alpha}^\alpha, K_{e,S}^\alpha$$

### Mixture model

$$\sum_\alpha f^\alpha = 1$$

$$\bar{\rho} = \sum_\alpha f^\alpha \rho^\alpha$$

$$\bar{C}_v = \frac{1}{\bar{\rho}} \sum_\alpha (f^\alpha \rho^\alpha C_{v,i}^\alpha)$$

$$1/K_S = \sum_\alpha (f^\alpha / K_S^\alpha)$$

$$P = \sum_\alpha \frac{f^\alpha P_{i,\alpha}^\alpha}{K_S^\alpha} / \sum_\alpha \frac{f^\alpha}{K_S^\alpha}$$

$$\bar{\rho} C_{v,i} / \bar{\rho}_i = \sum_\alpha (f^\alpha \rho^\alpha C_{v,i}^\alpha / \rho_i^\alpha)$$

$$\bar{T} = \sum_\alpha f^\alpha \rho^\alpha C_{v,i}^\alpha T^\alpha / \sum_\alpha f^\alpha \rho^\alpha C_{v,i}^\alpha$$



## Summary



- Model describes ablation depth for single pulse experiments.
- For long delays the second pulse interacts with nanoparticles (layers) in liquid phase.
- Back deposition of substance caused by the second pulse is the reason of even less crater depth for double pulses with long delay.
- **Second pulse shielding: substantial changes of transport properties or complex mechanical spallation?**

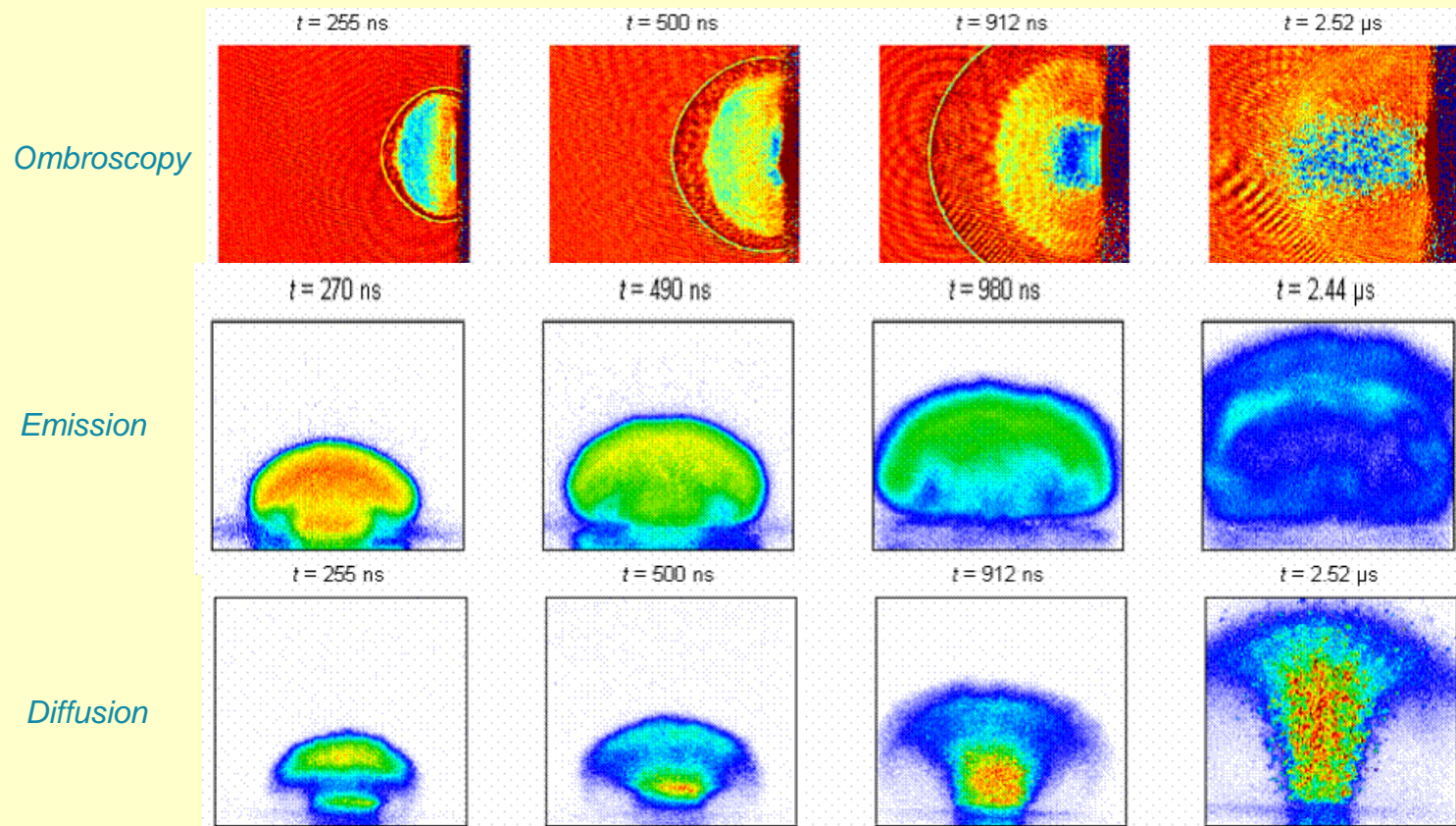


## Laser Plasma Chemistry and Dusts (nano/micro-particles) in Laser Plasmas

(theses of F. Chartier, of F. Brygo, of P. Dewalle)



## Plasma diagnostics



Paint,  $T_{\text{laser}}=100\text{ns}$ , Fluence= $10\text{J}/\text{cm}^2$

Results of Pascale Dewalle thesis, 2009,



## Conclusions

- ❑ The “dusts” (molecules, nano/micro-particles) effect on the laser plume characteristics is mandatory for an adequate modelling and description of the “LIBS plasma” analytical properties;
- ❑ Plasma chemistry (formation of the molecules and aggregates in the LIBS plasmas);
- ❑ Dusts (nano/micro-particles) ejection in the LIBS plasmas